MBR2020CT - MBR20100CT

20A DUAL SCHOTTKY BARRIER RECTIFIER

Features

- Power Schottky Barrier Chip
- Guard Ring for Transient Protection
- Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Current Capability
- Epoxy Meets UL 94V-0 Classification
- Ideally Suited for Use in High Frequency SMPS, Inverters and As Free Wheeling Diodes

Mechanical Data

Case: TO-220AB, Molded Plastic
Terminals: Plated Leads Solderable per

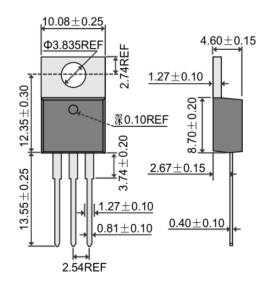
MIL-STD-202, Method 208 Polarity: See Diagram

Weight: 1.9 grams (approx.)

Mounting Position: AnyMounting Torque: 0.6 N.m Max.

Lead Free: For RoHS / Lead Free Version

TO-220AB





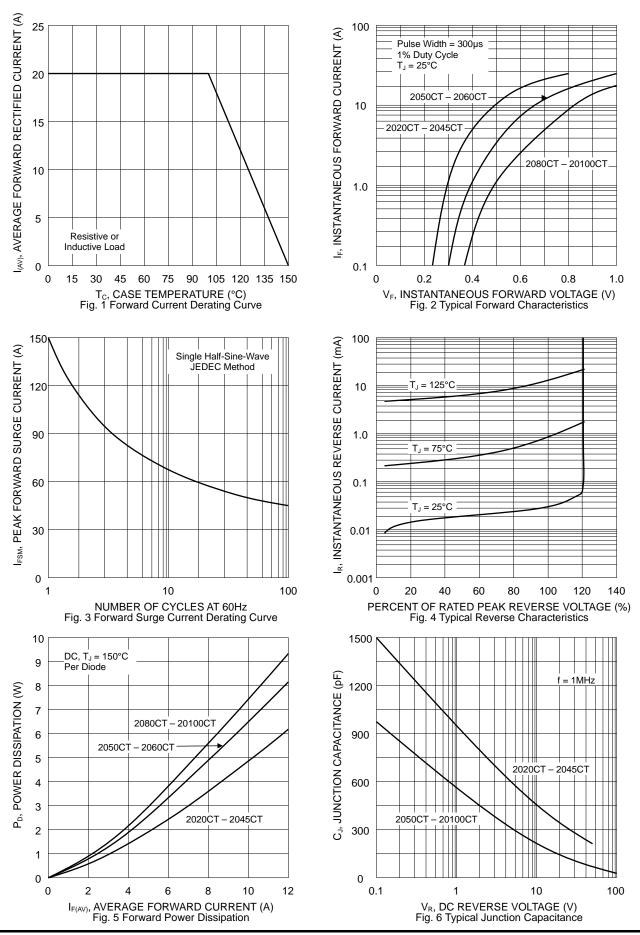
Maximum Ratings and Electrical Characteristics @TA=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

| Characteristic | Symbol | MBR 2020CT | MBR 2030CT | MBR 2040CT | MBR 2045CT | MBR 2050CT | MBR 2060CT | MBR 2080CT | MBR 20100CT | Unit |
|---|--------------------|------------------------|---------------|---------------|---------------|---------------|---------------|---------------|----------------|----------|
| Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage | VRRM VRWM VR | 20 | 30 | 40 | 45 | 50 | 60 | 80 | 100 | V |
| RMS Reverse Voltage | VR(RMS) | 14 | 21 | 28 | 32 | 35 | 42 | 56 | 70 | V |
| verage Rectified Output Current Total Device T _C = 100°C Per Diode Io 20 | | | | | | Α | | | | |
| Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load (JEDEC Method) | IFSM | 150 | | | | | А | | | |
| Forward Voltage $@I_F = 10A, T_J = 25^{\circ}C$ per diode $@I_F = 10A, T_J = 125^{\circ}C$ | VFM | 0.55 0.75 0.50 0.65 | | | | 0.85 0.75 | | V | | |
| Peak Reverse Current $@T_J = 25^{\circ}C$ At Rated DC Blocking Voltage $@T_J = 100^{\circ}C$ | IRM | 0.5 20 | | | | mA | | | | |
| Typical Junction Capacitance (Note 1) | Сл | 650 350 | | | | pF | | | | |
| Thermal Resistance Junction to Ambient per diode Thermal Resistance Junction to Case per diode | R JA R JC | 60 2.0 | | | °C/W | | | | | |
| Operating and Storage Temperature Range | TJ, TSTG | -55 to +150 | | | | | | °C | | |

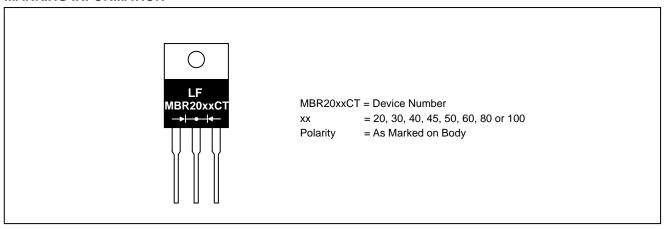
Note: 1. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

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MARKING INFORMATION



PACKAGING INFORMATION

BULK

| Tube Size L x W x H (mm) | Quantity (PCS) | Inner Box Size L x W x H (mm) | Quantity (PCS) | Carton Size L x W x H (mm) | Quantity (PCS) | Approx. Gross Weight (KG) |
|-----------------------------|-------------------|----------------------------------|-------------------|-------------------------------|-------------------|---------------------------|
| 525 x 31 x 6 | 50 | 558 x 150 x 40 | 1,000 | 570 x 235 x 170 | 5,000 | 11.85 |

RECOMMENDED SCREW MOUNTING ARRANGEMENT

Recommended isolated mounting when screw is at heatsink potential. 4-40 hardware is used.

Screw should not be tightened with any type of air-forced torque or equipment that may cause high impact on device package. The insulating bushing inside the mounting hole will insure the screw threads do not contact the metal base.

The interface should apply a layer of thermal grease or a highly conductive thermal pad for better heat dissipation.

